



IRF9Z20PBF Information



For Reference Only

Part Number IRF9Z20PBF
Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET P-CH 50V 9.7A TO-220AB

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRF9Z20PBF Specifications

Manufacturer Part Number IRF9Z20PBF Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 50V Current - Continuous Drain (Id) @ 25°C 9.7A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 26nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 480pF @ 25V Vgs (Max) + 20V FET Feature - Power Dissipation (Max) 40W (Tc) Rds On (Max) @ Id, Vgs 280 mOhm @ 5.6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3 Report errors?		
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Series-FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)50VCurrent - Continuous Drain (Id) @ 25°C9.7A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vgs26nC @ 10VInput Capacitance (Ciss) (Max) @ Vds480pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)40W (Tc)Rds On (Max) @ Id, Vgs280 mOhm @ 5.6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3		Transistors - FETs, MOSFETs - Single
FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)50VCurrent - Continuous Drain (Id) @ 25°C9.7A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs26nC @ 10VInput Capacitance (Ciss) (Max) @ Vds480pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)40W (Tc)Rds On (Max) @ Id, Vgs280 mOhm @ 5.6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Package	TO-220-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)50VCurrent - Continuous Drain (Id) @ 25°C9.7A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs26nC @ 10VInput Capacitance (Ciss) (Max) @ Vds480pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)40W (Tc)Rds On (Max) @ Id, Vgs280 mOhm @ 5.6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Series	-
Drain to Source Voltage (Vdss)50VCurrent - Continuous Drain (Id) @ 25°C9.7A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs26nC @ 10VInput Capacitance (Ciss) (Max) @ Vds480pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)40W (Tc)Rds On (Max) @ Id, Vgs280 mOhm @ 5.6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C9.7A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs26nC @ 10VInput Capacitance (Ciss) (Max) @ Vds480pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)40W (Tc)Rds On (Max) @ Id, Vgs280 mOhm @ 5.6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-220AB TO-220-3	Drain to Source Voltage (Vdss)	50V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 4V @ 250μA 480 P @ 25V 480pF @ 25V	Current - Continuous Drain (Id) @ 25°C	9.7A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 480pF @ 25V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 280 mOhm @ 5.6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-220AB TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 280 mOhm @ 5.6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)40W (Tc)Rds On (Max) @ Id, Vgs280 mOhm @ 5.6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	26nC @ 10V
FET Feature - Power Dissipation (Max) 40W (Tc) Rds On (Max) @ Id, Vgs 280 mOhm @ 5.6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	480pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs280 mOhm @ 5.6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Power Dissipation (Max)	40W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	280 mOhm @ 5.6A, 10V
Supplier Device Package TO-220AB Package / Case TO-220-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
		Report errors?

IRF9Z20PBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRF9Z20PBF Payment Methods



















IRF9Z20PBF Shipping Methods













If you have any question about IRF9Z20PBF, please do not hesitate to contact us!

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